Abstracts

High Efficiency, Low Adjacent Channel Leakage GaAs Power MMIC for Digital Cordless Telephone

T. Kunihisa, T. Yokoyama, H. Fujimoto, K. Ishida, H. Takehara and O. Ishikawa. "High Efficiency, Low Adjacent Channel Leakage GaAs Power MMIC for Digital Cordless Telephone." 1994 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 94.1 (1994 [MCS]): 55-58.

This paper presents the high efficiency, low spectrum distortion surface mount plastic packaged GaAs power MMIC for 1.9GHz band Japanese digital cordless telephone. Two power MESFETs and input, lnterstage and output matching circuits are integrated in very small single chip of 1.0 mm x 1.5mm. The power MMIC achieves high power added efficiency (PAE) of 40.5% with low adjacent channel leakage power (Padj) of -56dBc at Pout=22dBm under Iow operating voltage of 3.0V.

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